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View Online at https://aerobasegroup.com/nsn/5961-01-096-1130

Inclosure Material:

Metal

Overall Length:

1.573 inches

Overall Height:

0.450 inches

Overall Width:

1.050 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

7.0 emitter to base voltage, static, collector open and 60.0 breakdown voltage, collector-to-emitter, base open

Current Rating Per Characteristic:

15.00 amperes source cutoff current and 7.00 amperes source cutoff current

Power Rating Per Characteristic:

117.0 watts small-signal input power, common-collector preset

Transfer Ratio:

70.0 static forward current transfer ratio, common-emitter

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Terminal Type And Quantity:

2 pin and 1 case

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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